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PTO/SB/30 (5/2000)
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REQUEST FOR CONTINUED EXAMINATION (RCE)

Subsection (b) of 35 U.S.C. §132, effective on May 29, 2000, provides for continued examination of a utility or plant application filed on or after June 8, 1995. See The American Inventors Protection Act of 1999 (AIPA).

Application Number	09/852,672
Filing Date	May 11, 2001
First Named Inventor	Hideomi Suzawa et al.
Group Art Unit	2812
Examiner Name	Viktor Simkovic
Attorney Docket Number	12732-038001

This is a Request for Continued Examination (RCE) under 37 C.F.R. §1.114 of the above-identified application.

NOTE: 37 C.F.R. §1.114 is effective on May 29, 2000. If the above-identified application was filed prior to May 29, 2000, applicant may wish to consider filing a continued prosecution application (CPA) under 37 C.F.R. §1.53(d) (PTO/SB/29) instead of a RCE to be eligible for the patent term adjustment provisions of the AIPA. See Changes to Application Examination and Provisional Application Practice, Interim Rule, 65 Fed. Reg. 14865 (Mar. 20, 2000), 1233 Off. Gaz. Pat. Office 47 (Apr. 11, 2000), which established RCE practice.

1. Submission required under 37 C.F.R. §1.114
   - a. ☐ Previously submitted
     - i. ☐ Consider the amendment(s)/reply under 37 C.F.R. §1.116 previously filed on _____ (Any unentered amendment(s) referred to above will be entered)
     - ii. ☐ Consider the arguments in the Appeal Brief or Reply Brief previously filed on _____
     - iii. ☐ Other _____
   - b. ☒ Enclosed
     - i. ☒ Amendment/Reply
     - ii. ☐ Affidavit(s)/Declaration(s)
     - iii. ☒ Information Disclosure Statement (IDS)
     - iv. ☒ Other Petition for Two-Month Extension of Time with $410 Fee

2. Miscellaneous
   - a. ☐ Suspension of action on the above-identified application is requested under 37 C.F.R. §1.103(c) for a period of _____ months. (Period of suspension shall not exceed 3 months; fee under 37 C.F.R. §1.17(i) **required**)
   - b. ☐ Other _

3. Fee — The RCE fee under 37 C.F.R. §1.17(e) is required by 37 C.F.R. §1.114 when the RCE is filed.
   - a. ☒ The Director is hereby authorized to charge the following fees, or credit any overpayments, to Deposit Account No. 06-1050
     - i. ☐ RCE fee required under 37 C.F.R. §1.17(e)
     - ii. ☐ Extension of time fee (37 C.F.R. §§1.136 and 1.17)
     - iii. ☒ Other Any deficiencies
   - b. ☒ Check in the amount of $ 1160 enclosed
   - c. ☐ Payment by credit card (Form PTO-2038 enclosed)

SIGNATURE OF APPLICANT, ATTORNEY OR AGENT REQUIRED

Name (Print/Type)	John F. Hayden	Registration No. (Attorney/Agent)	37,640
Signature		Date	March 20, 2003

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THE UNITED STATES PATENT AND TRADEMARK OFFICE

#15/B
3-31-03
Paxton

Applicant : Hideomi Suzawa et al.
Serial No. : 09/852,672
Filed : May 11, 2001
Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Art Unit : 2812
Examiner : Viktor Simkovic

BOX AF
Commissioner for Patents
Washington, D.C. 20231

RESPONSE

In response to the action mailed November 6, 2002, please amend the application as follows:

In the claims:

Please amend claims 9 and 18 as follows:

-- 9. (Amended) A method of manufacturing a semiconductor device comprising steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

forming a first electrode comprising a laminate structure of a first conductive layer with a first width and a second conductive layer on said insulating film;

adding an impurity element to said semiconductor layer using said first electrode as a mask to form a high concentration impurity region;

etching said second conductive layer to form a second electrode comprising a laminate structure of the first conductive layer with said first width and said second conductive layer with a second width;

adding the impurity element to said semiconductor layer using said second conductive layer as a mask to form a low concentration impurity region; and

after forming the low concentration impurity region, etching said first conductive layer to form a third electrode comprising a laminate structure of said first conductive layer with a third width and said second conductive layer with said second width.